

IN THE CLAIMS

Please amend the claims, and add new claims 22 to 25, as follows:

1. (currently amended) A quartz [Quartz] glass crucible for crystal pulling, said crucible comprising: [with] a crucible wall, comprising an outer layer of opaque quartz glass and an inner layer, wherein the outer layer has an inner region and an outer region, said outer layer being [which is] provided with a crystallization promoter that effects crystallization of quartz glass with formation of cristobalite when the quartz glass crucible is heated during said [intended use in] crystal pulling, [characterized in that] wherein the crystallization promoter contains a first component other than silicon that acts [acting] in quartz glass [~~—additionally to silicon—~~] as a network former [~~and/~~] or a network modifier [~~in quartz glass~~] and a second, alkali-metal-free component that acts [acting] in quartz glass as a breakpoint former, and wherein [that] the outer layer [(6) comprises] has a doping region [(8)] having a layer thickness of more than 0.2 mm and containing said components [~~being~~] entrapped therein.
2. (currently amended) A quartz [Quartz] glass crucible according to claim 1, [characterized in that] wherein the first component acts [acting] as a network former and contains a tetravalent substance.
3. (currently amended) A quartz [Quartz] glass crucible according to claim 2, [characterized in that] wherein the tetravalent substance comprises one or more elements from the group consisting of [is] titanium (Ti^{4+}), zirconium (Zr^{4+}), hafnium (Hf^{4+}), germanium (Ge^{4+}) and [~~for~~] tin (Sn^{4+}).
4. (currently amended) A quartz [Quartz] glass crucible according to claim 1, [characterized in that] wherein the second component [~~acting as breakpoint former~~] contains a divalent [~~alkali-free-metal~~] substance that does not contain alkali metal.

5. (currently amended) A quartz [Quartz] glass crucible according to claim 4, ~~[characterized in that]~~ wherein the divalent ~~[, alkali-metal-free]~~ substance comprises one or more elements from the group consisting of ~~[is]~~ barium (Ba^{2+}) and~~[or]~~ strontium.
6. (currently amended) A quartz [Quartz] glass crucible according to claim 1 ~~[one of claims 1 to 5]~~, ~~[characterized in that]~~ wherein the first component and the second component each have a distribution coefficient in silicon of 10^{-5} or less ~~[max]~~.
7. (currently amended) A quartz [Quartz] glass crucible according to claim 1 ~~[one of claims 1 to 6]~~, ~~[characterized in that]~~ wherein the first component and the second component are each contained in a concentration ranging from 0.003 mol-% to 0.02 mol-% in the doping region.
8. (currently amended) A quartz [Quartz] glass crucible according to claim 1 ~~[one of claims 1 to 7]~~, ~~[characterized in that]~~ wherein the first component and the second component are contained in the doping region ~~[(8)]~~ in the form of an oxide compound containing the said components.
9. (currently amended) A quartz [Quartz] glass crucible according to claim 8, ~~[characterized in that]~~ wherein the oxide compound consists of a ternary oxide ~~[, such as barium titanate (BaTiO_3) or barium zirconate (BaZrO_3) or a mixture thereof]~~.
10. (currently amended) A quartz [Quartz] glass crucible according to claim 1 ~~[one of claims 1 to 9]~~, ~~[characterized in that]~~ wherein the doping region ~~[(8)]~~ has a layer thickness of more than 0.5 mm ~~[, preferably more than 2 mm]~~.
11. (currently amended) A quartz [Quartz] glass crucible according to claim 10, ~~[characterized in that]~~ wherein the layer thickness is 10 mm or less ~~[max]~~.
12. (currently amended) A quartz [Quartz] glass crucible according to claim 1 ~~[one of claims 1 to 11]~~, ~~[characterized in that]~~ wherein the quartz glass crucible has an essentially cylindrical side wall ~~[(4)]~~ about the axis of rotation ~~[(1)]~~, and wherein the doping region ~~[(8)]~~ is formed as a doping strip in the side wall ~~[(4)]~~.

13. (currently amended) **A method** [~~Method~~] for manufacturing a quartz glass crucible [~~according to one of claims 1 to 12 by~~] **said method comprising** producing a crucible base body comprising an outer layer of opaque quartz glass and an inner layer, wherein at least part of the outer layer in an outer region surrounding an inner region is provided with a crystallization promoter which, on heating of the quartz glass crucible during **said** [~~intended use in~~] crystal pulling, causes crystallization of quartz glass with formation of cristobalite, [~~characterized in that~~] **wherein** a first component **other than silicon that acts** [~~acting~~] in quartz glass [~~—additionally to silicon—~~] as **a** network former [~~and/~~]or [~~in quartz glass~~] as **a** network modifier, and an alkali-metal-free second component acting as breakpoint former in quartz glass **are** [~~is~~] used as **to promote** crystallization [~~promoter~~], and **wherein** [~~that~~] said components are introduced into and entrapped in a doping region [(8)] of the outer layer [(6)], **said doping layer** having a layer thickness of more than 0.2 mm.
14. (currently amended) **A method** [~~Method~~] according to claim 13, [~~characterized in that an~~] **wherein the** outer layer [(6)] having the doping region [(8)] is generated [~~in that~~] **by introducing** SiO₂ grains [~~are introduced~~] into a melting mold **so as to be** [~~and~~] shaped therein into a crucible-shaped layer of SiO₂ grains, wherein said components are added to the SiO₂ grains before shaping of the doping region [(8)], and then the layer of SiO₂ grains is sintered **so as to form** [~~with formation of~~] the outer layer [(G)].
15. (currently amended) **A method** [~~Method~~] according to **claim 13** [~~one of claims 13 or 14~~], [~~characterized in that~~] **wherein** a tetravalent substance **that acts as a network former** is used as the [~~network-forming~~] first component.
16. (currently amended) **A method** [~~Method~~] according to claim 15, [~~characterized in that~~] **wherein** the tetravalent substance [~~is~~] **comprises one or more elements selected from the group consisting of** titanium (Ti⁴⁺), zirconium (Zr⁴⁺), hafnium (Hf⁴⁺), germanium (Ge⁴⁺) and [~~or~~] tin (Sn⁴⁺).
17. (currently amended) **A method** [~~Method~~] according to **claim 13** [~~one of claims 13 to 16~~], [~~characterized in that~~] **wherein** the second component [~~acting as breakpoint~~]

~~former~~] contains a divalent [~~alkali-free-metal~~] substance that does not contain any alkali metal.

18. (currently amended) A method [~~Method~~] according to claim 17, [~~characterized in that~~] wherein the divalent substance comprises one or more elements from the group consisting of [~~is~~] barium (Ba^{2+}) and [~~or~~], strontium.
19. (currently amended) A method [~~Method~~] according to claim 13 [~~one of claims 13 to 18~~], [~~characterized in that~~] wherein the first component and the second component are each introduced in a concentration ranging from 0.003 mol-% to 0.02 mol-% in the doping region.
20. (currently amended) A method [~~Method~~] according to claim 13 [~~one of claims 13 to 19~~], [~~characterized in that~~] wherein the first component and the second component are contained in the doping region [~~(8)~~] of the outer layer [~~(6)~~] in the form of an oxide compound containing said components.
21. (currently amended) A method [~~Method~~] according to claim 20, [~~characterized in that~~] wherein the oxide compound consists essentially of a ternary oxide [~~, such as barium titanate (BaTiO_3) or barium zirconate (BaZrO_3) or a mixture thereof~~].
22. (new) A method according to claim 21, wherein the ternary oxide is barium titanate (BaTiO_3), barium zirconate (BaZrO_3), or a mixture thereof.
23. (new) A quartz glass crucible according to claim 8, wherein the ternary oxide is barium titanate (BaTiO_3), barium zirconate (BaZrO_3), or a mixture thereof.
24. (new) A quartz glass crucible according to claim 1, wherein the doping region has a layer thickness of more than 2 mm.
25. (new) A quartz glass crucible according to claim 24, wherein the layer thickness is 10 mm or less.